2SD1504

Silicon NPN Epitaxial

HITACHI

Application

Low frequency amplifier, Muting

Outline

SPAK



- 1. Emitter
- 2. Collector
- 3. Base



2SD1504

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	30	V	
Collector to emitter voltage	V _{CEO}	15	V	
Emitter to base voltage	V_{EBO}	5	V	
Collector current	I _c	0.5	А	
Collector peak current	ic (peak)	1.0	А	
Collector power dissipation	P _c	300	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

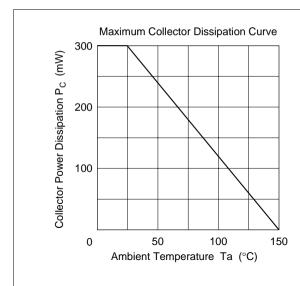
Electrical Characteristics (Ta = 25°C)

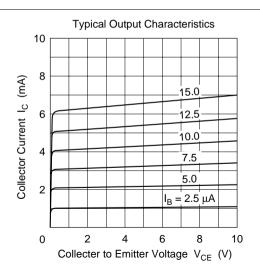
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	15	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	10	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE} *1	250	_	1200		$V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	_	0.65	_	V	$V_{CE} = 1 \text{ V}, I_{C} = 150 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.15	0.5	V	$I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 50 mA* ²
	V _{CE(sat)}	_	0.018	_	V	$I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 3 \text{ mA}$
Gain bandwidth product	f _T	_	300	_	MHz	$V_{CE} = 1 \text{ V}, I_{C} = 50 \text{ mA}$
On resistance	r _{on}	_	0.5	_	Ω	I _B = 2 mA

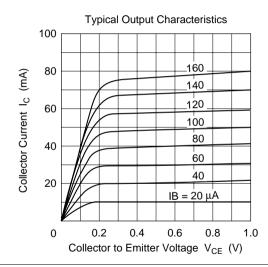
Notes: 1. The 2SD1504 is grouped by h_{FE} as follows.

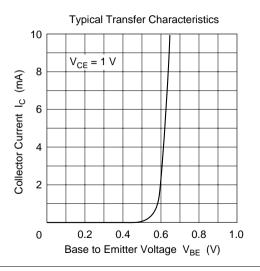
2. Pulse test

D	E	F
250 to 500	400 to 800	600 to 1200

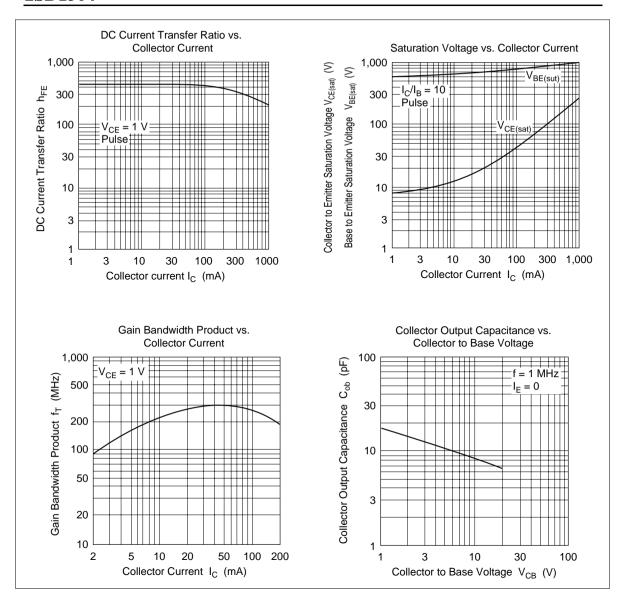


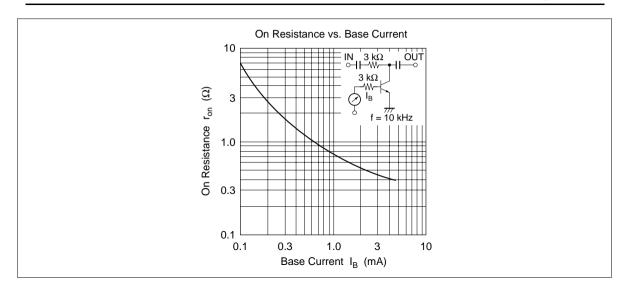


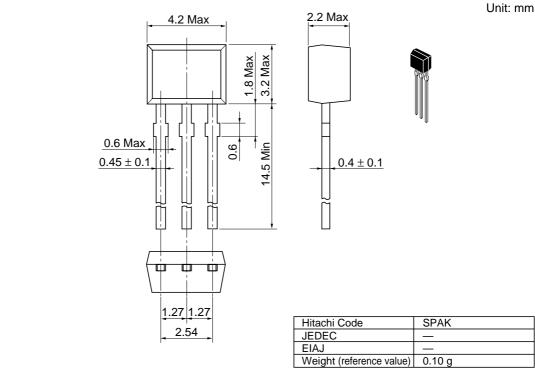




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